

Notice of References Cited	Application/Control No. 10/802,185	Applicant(s)/Patent Under Reexamination CHENG ET AL.	
	Examiner Craig A. Thompson	Art Unit 2813	Page 1 of 1

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*		Document Number Country Code-Number-Kind Code	Date MM-YYYY	Name	Classification
*	A	US-5,923,046	07-1999	Tezuka et al.	257/24
	B	US-			
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	D	US-			
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	I	US-			
	J	US-			
	K	US-			
	L	US-			
	M	US-			

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	N	JP409219524A	08-1997	Japan	IMAI et al.	H01L 29/786
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NON-PATENT DOCUMENTS

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	U	JPAB English Language Abstract of JP409219524A, Aug 19, 1997.
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*A copy of this reference is not being furnished with this Office action. (See MPEP § 707.05(a).)
Dates in MM-YYYY format are publication dates. Classifications may be US or foreign.